CLAIMS

[1] A two-beam semiconductor laser device comprising:

a two-beam semiconductor element having a first and a second semiconductor laser elements that can be driven independently and that are formed integrally on a substrate; and

a submount having, mounted on a front part thereof, the two-beam semiconductor laser element with a light-emitting face thereof directed forward and having a first and a second electrode pads connected to electrodes of the first and second semiconductor laser element by being kept in contact therewith,

wherein the first and second electrode pads are formed to extend farther behind the two-beam semiconductor laser element, and are wire-bonded behind the two-beam semiconductor laser element.

[2] The two-beam semiconductor laser device of claim 1,

wherein the first and second electrode pads are wire-bonded at a rear end of the submount.

[3] The two-beam semiconductor laser device of claim 1 or 2,

wherein a distance from the rear end of the two-beam semiconductor laser element to a position where the first and second electrode pads are wire-bonded is 300 μm or shorter.

[4] The two-beam semiconductor laser device of one of claims 1 to 3,

wherein a lateral length of the submount is 400 μm or more but 700 μm or less.

[5] The two-beam semiconductor laser device of one of claims 1 to 4,

wherein the submount is mounted in a package composed of a frame and a resin member.

[6] The two-beam semiconductor laser device of claim 5,

wherein the two-beam semiconductor laser device is built as a three-terminal two-beam semiconductor laser device having three terminals.